

OptiMOS[®]-P Small-Signal-Transistor Feature

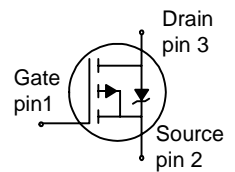
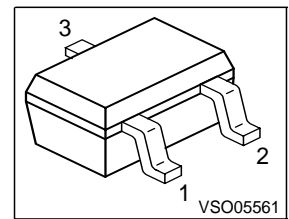
- P-Channel
- Enhancement mode
- Super Logic Level (2.5 V rated)
- 150°C operating temperature
- Avalanche rated
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21



Product Summary

V_{DS}	-20	V
$R_{DS(on)}$	1.2	Ω
I_D	-0.39	A

PG-SOT-323



Type	Package	Tape and Reel	Marking
BSS 223PW	PG-SOT-323	H6327:3000pcs/r.	X4s

Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D		A
$T_A=25\text{ }^\circ\text{C}$		-0.39	
$T_A=70\text{ }^\circ\text{C}$		-0.31	
Pulsed drain current	$I_{D\text{ puls}}$	-1.56	
$T_A=25\text{ }^\circ\text{C}$			
Avalanche energy, single pulse	E_{AS}	1.4	mJ
$I_D=-0.39\text{ A}$, $V_{DD}=-10\text{ V}$, $R_{GS}=25\Omega$			
Reverse diode dv/dt	dv/dt	-6	kV/ μs
$I_S=-0.39\text{ A}$, $V_{DS}=-16\text{ V}$, $di/dt=200\text{ A}/\mu\text{s}$, $T_{j\text{max}}=150\text{ }^\circ\text{C}$			
Gate source voltage	V_{GS}	± 12	V
Power dissipation	P_{tot}	0.25	W
$T_A=25\text{ }^\circ\text{C}$			
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class; JESD22-A114-HBM		Class 0	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	-	180	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	500	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0, I_D=-250\mu\text{A}$	$V_{(BR)DSS}$	-20	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=-1.5\mu\text{A}$	$V_{GS(th)}$	-0.6	-0.9	-1.2	
Zero gate voltage drain current $V_{DS}=-20\text{V}, V_{GS}=0, T_j=25^\circ\text{C}$ $V_{DS}=-20\text{V}, V_{GS}=0, T_j=150^\circ\text{C}$	I_{DSS}	-	-0.1 -10	-1 -100	μA
Gate-source leakage current $V_{GS}=-12\text{V}, V_{DS}=0$	I_{GSS}	-	-10	-100	
Drain-source on-state resistance $V_{GS}=-2.5\text{V}, I_D=-0.29\text{A}$	$R_{DS(on)}$	-	1.27	2.1	Ω
Drain-source on-state resistance $V_{GS}=-4.5, I_D=-0.39\text{A}$	$R_{DS(on)}$	-	0.7	1.2	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$ V_{DS} \geq 2 * I_D * R_{DS(on)max}$ $I_D = -0.31\text{A}$	0.35	0.7	-	S
Input capacitance	C_{iss}	$V_{GS} = 0, V_{DS} = -15\text{V},$ $f = 1\text{MHz}$	-	45	56	pF
Output capacitance	C_{oss}		-	21	26	
Reverse transfer capacitance	C_{rss}		-	17	22	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10\text{V}, V_{GS} = -4.5\text{V},$ $I_D = -0.39\text{A}, R_G = 6\Omega$	-	3.8	5.7	ns
Rise time	t_r		-	5	7.5	
Turn-off delay time	$t_{d(off)}$		-	5.1	7.6	
Fall time	t_f		-	3.2	4.8	

Gate Charge Characteristics

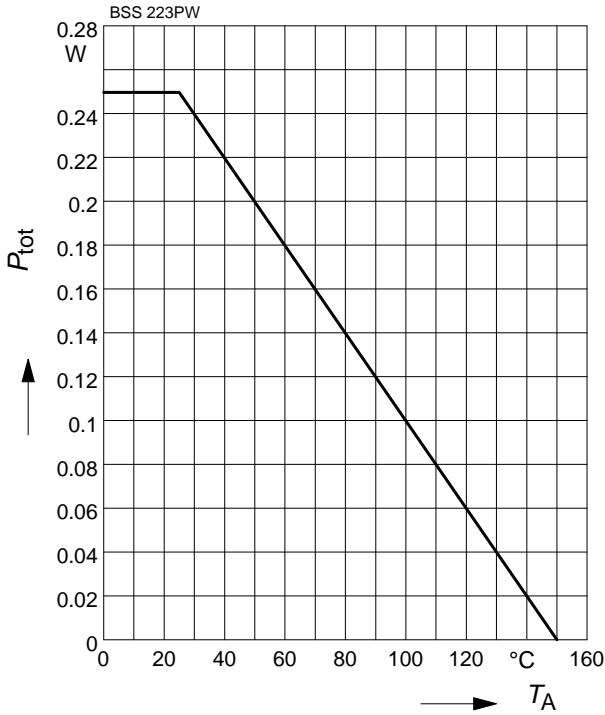
Gate to source charge	Q_{gs}	$V_{DD} = -10\text{V}, I_D = -0.39\text{A}$	-	-0.04	-0.05	nC
Gate to drain charge	Q_{gd}		-	-0.4	-0.5	
Gate charge total	Q_g	$V_{DD} = -10\text{V}, I_D = -0.39\text{A},$ $V_{GS} = 0 \text{ to } -4.5\text{V}$	-	-0.5	-0.62	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = -10\text{V}, I_D = -0.39\text{A}$	-	-2.2	-2.7	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_A = 25\text{ }^\circ\text{C}$	-	-	-0.39	A
Inv. diode direct current, pulsed	I_{SM}		-	-	-1.56	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0, I_F = -0.39$	-	-1	-1.33	V
Reverse recovery time	t_{rr}	$V_R = -10\text{V}, I_F = I_D ,$ $di_F/dt = 100\text{A}/\mu\text{s}$	-	7.6	9.5	ns
Reverse recovery charge	Q_{rr}		-	1.1	1.4	

1 Power dissipation

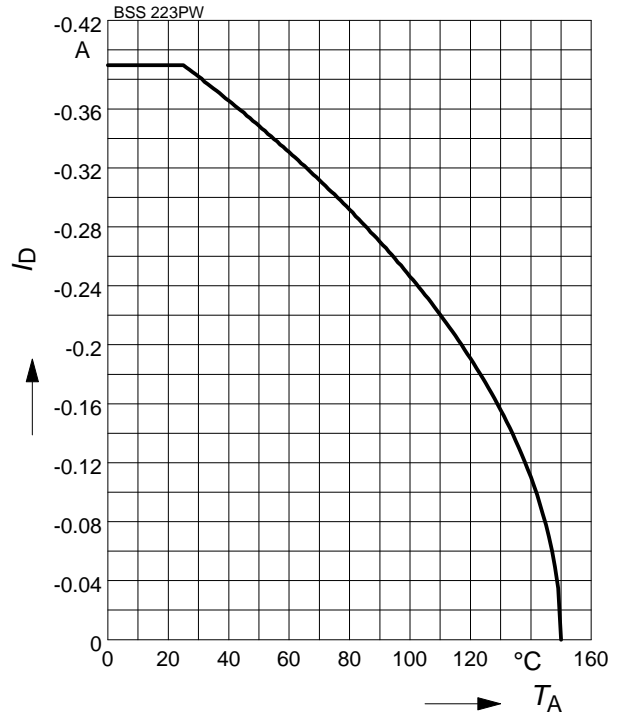
$P_{tot} = f(T_A)$



2 Drain current

$I_D = f(T_A)$

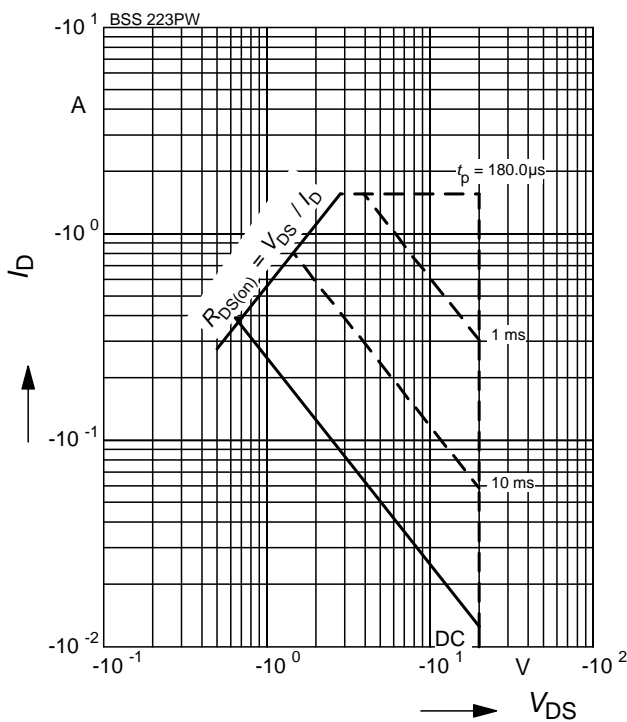
parameter: $|V_{GS}| \geq 4.5 \text{ V}$



3 Safe operating area

$I_D = f(V_{DS})$

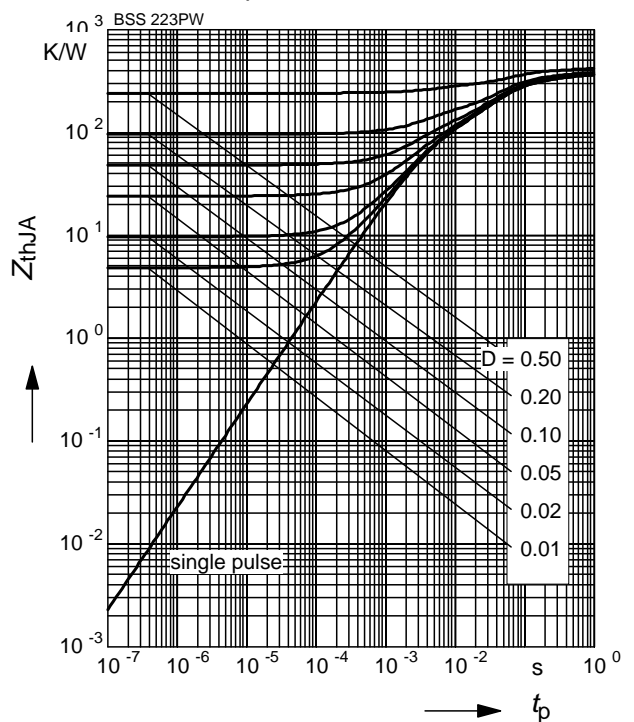
parameter: $D = 0, T_A = 25 \text{ °C}$



4 Transient thermal impedance

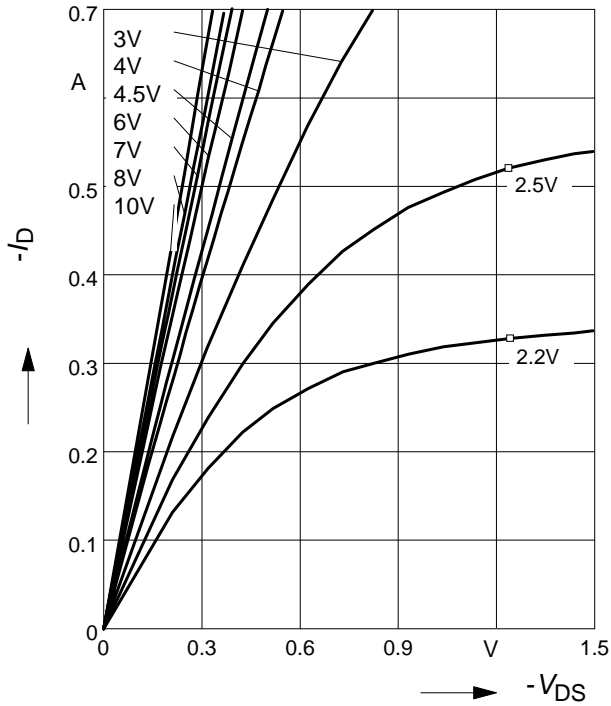
$Z_{thJA} = f(t_p)$

parameter: $D = t_p/T$



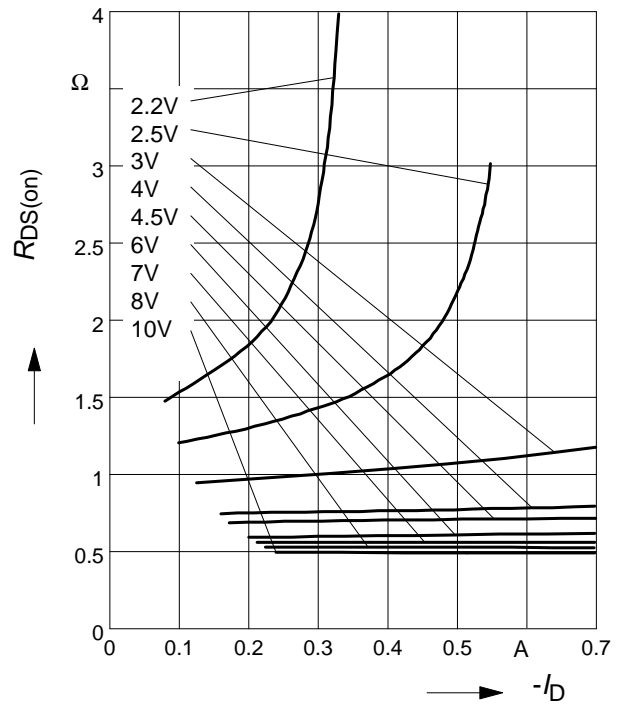
5 Typ. output characteristic

$I_D = f(V_{DS})$
parameter: $T_j = 25^\circ\text{C}$



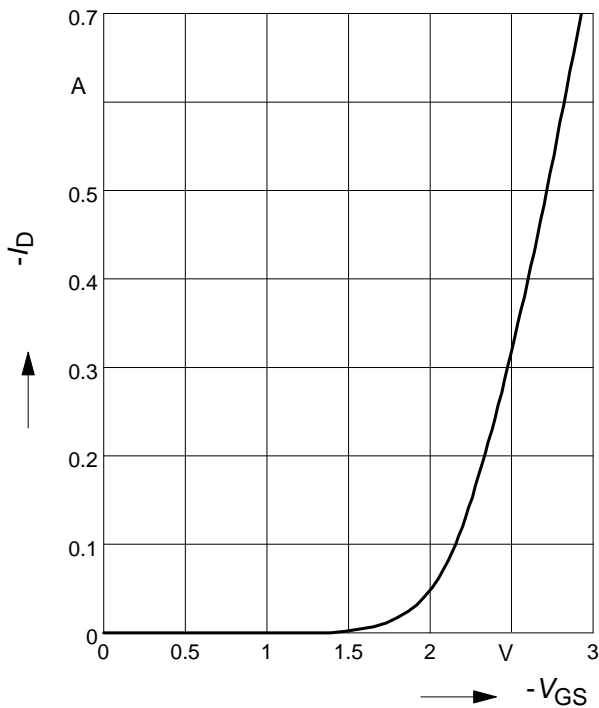
6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$
parameter: V_{GS}



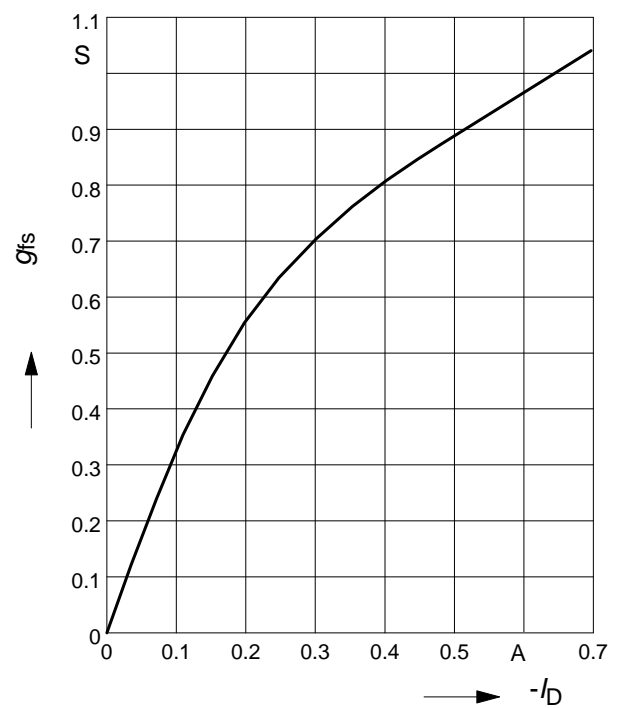
7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $|V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$
parameter: $T_j = 25^\circ\text{C}$



8 Typ. forward transconductance

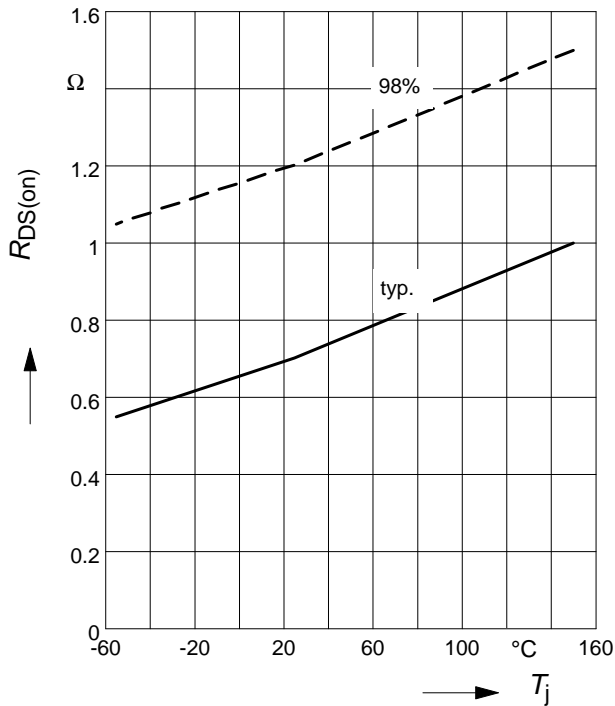
$g_{fs} = f(I_D)$
parameter: $T_j = 25^\circ\text{C}$



9 Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

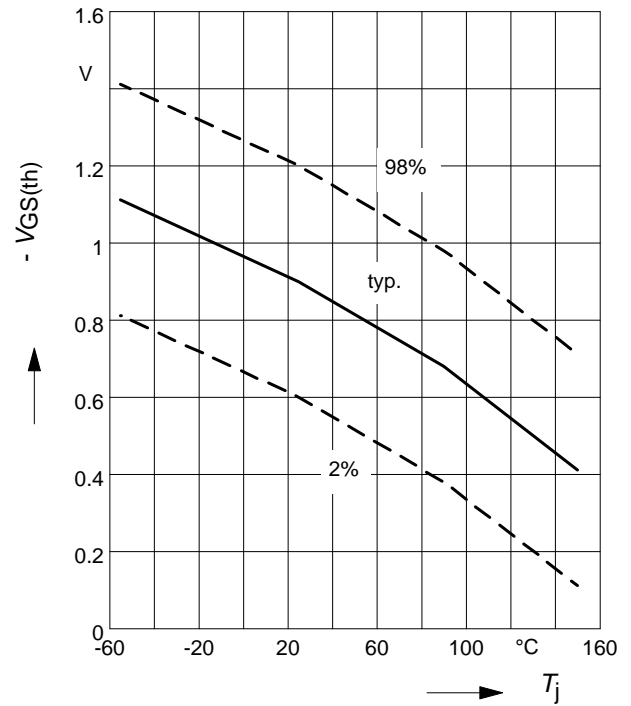
parameter: $I_D = -0.39$ A, $V_{GS} = -4.5$ V



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

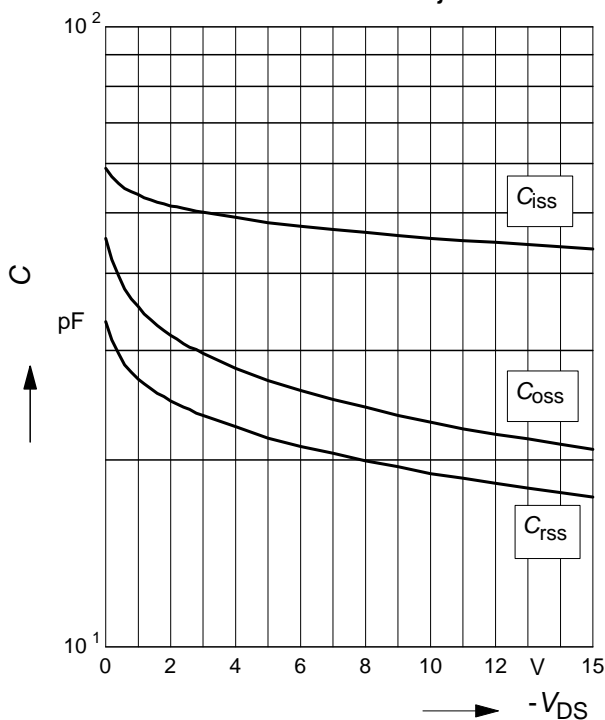
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

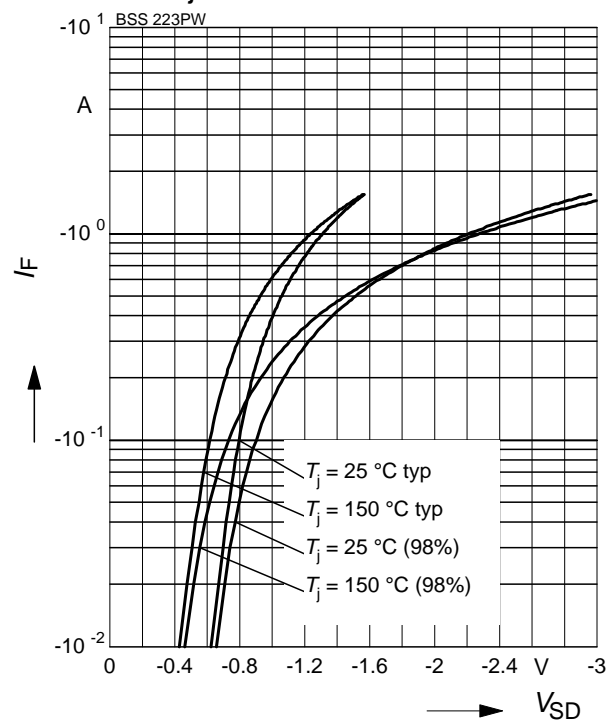
parameter: $V_{GS}=0$, $f=1$ MHz; $T_j = 25$ °C



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

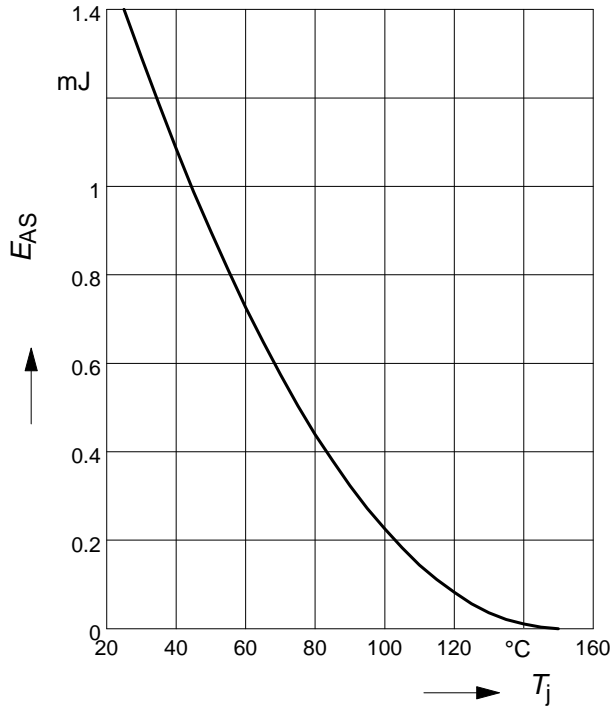
parameter: T_j



13 Typ. avalanche energy

$E_{AS} = f(T_j)$, par.: $I_D = -0.39$ A

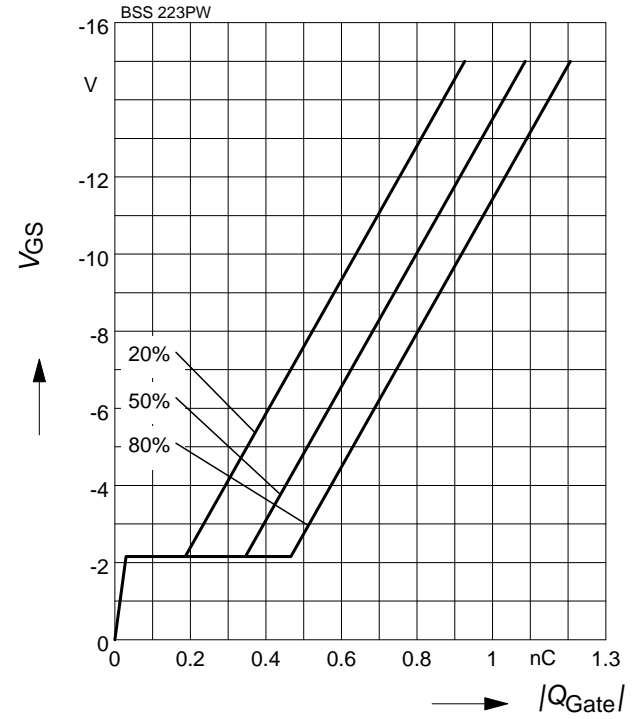
$V_{DD} = -10$ V, $R_{GS} = 25$ Ω



14 Typ. gate charge

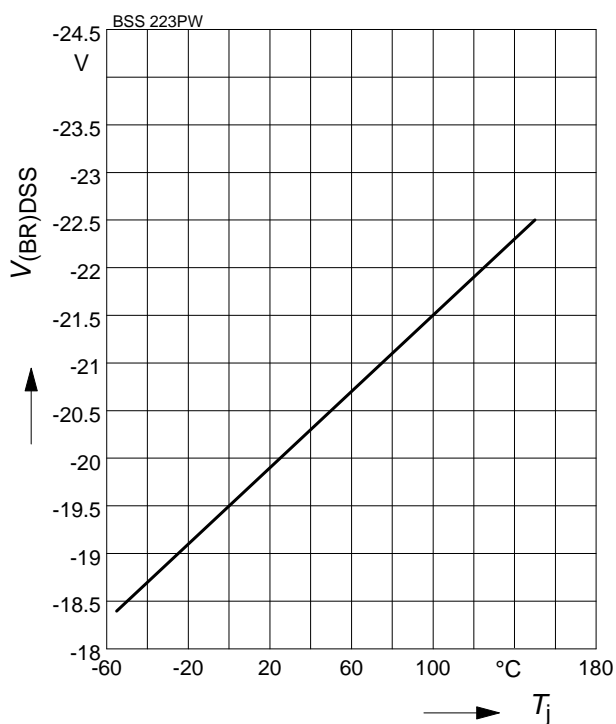
$V_{GS} = f(Q_{Gate})$

parameter: $I_D = -0.39$ A pulsed; $T_j = 25$ °C



15 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$



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Infineon Technologies AG
81726 Munich, Germany
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